

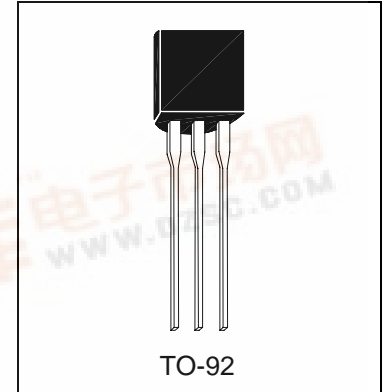


# HI-SINCERITY MICROELECTRONICS CORP.

Spec. No. : HE6464  
 Issued Date : 1993.09.07  
 Revised Date : 2005.02.15  
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## HT666

NPN EPITAXIAL PLANAR TRANSISTOR



### Description

The HT666 is designed for general purpose amplifier and high-speed, medium-power switching applications.

### Features

- High Frequency Current Gain
- High Speed Switching Transistor

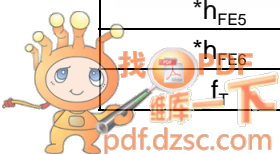
### Absolute Maximum Ratings

- Maximum Temperatures  
 Storage Temperature ..... -55 ~ +150 °C  
 Junction Temperature ..... +150 °C Maximum
- Maximum Power Dissipation  
 Total Power Dissipation (T<sub>A</sub>=25°C) ..... 625 mW
- Maximum Voltages and Currents (T<sub>A</sub>=25°C)  
 BV<sub>CBO</sub> Collector to Base Voltage ..... 75 V  
 BV<sub>CEO</sub> Collector to Emitter Voltage ..... 40 V  
 BV<sub>EBO</sub> Emitter to Base Voltage ..... 6 V  
 I<sub>C</sub> Collector Current ..... 600 mA

### Electrical Characteristics (T<sub>A</sub>=25°C)

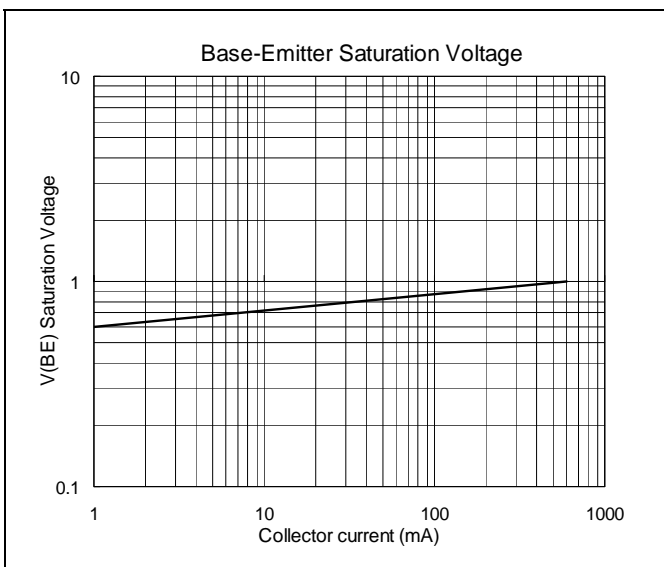
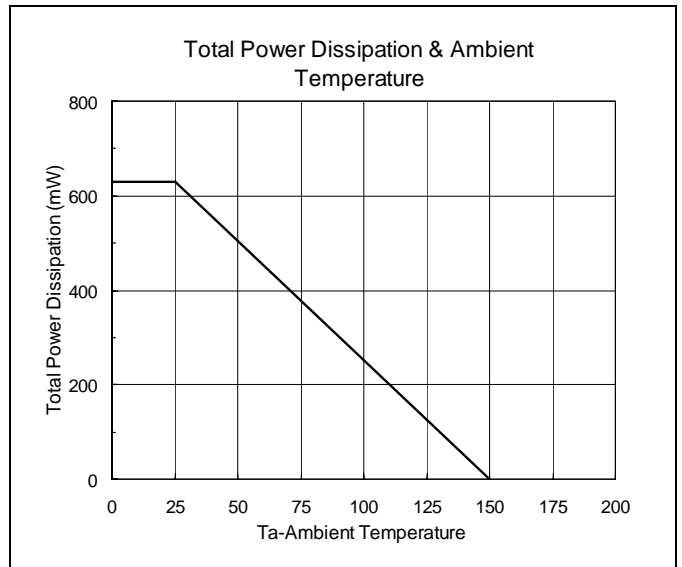
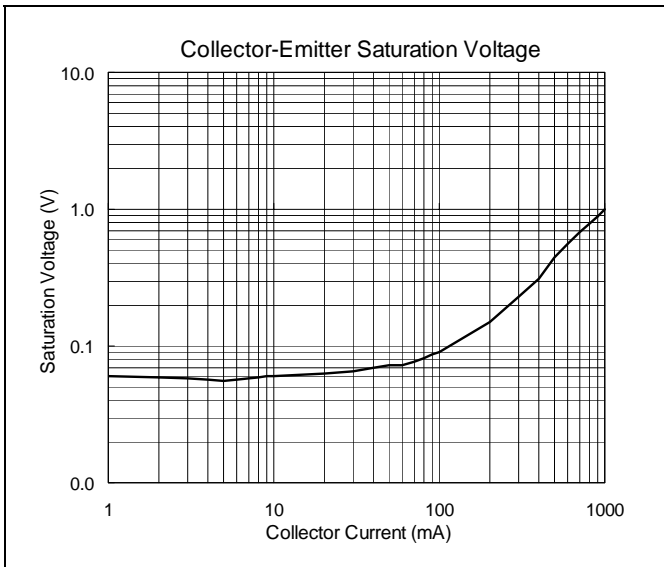
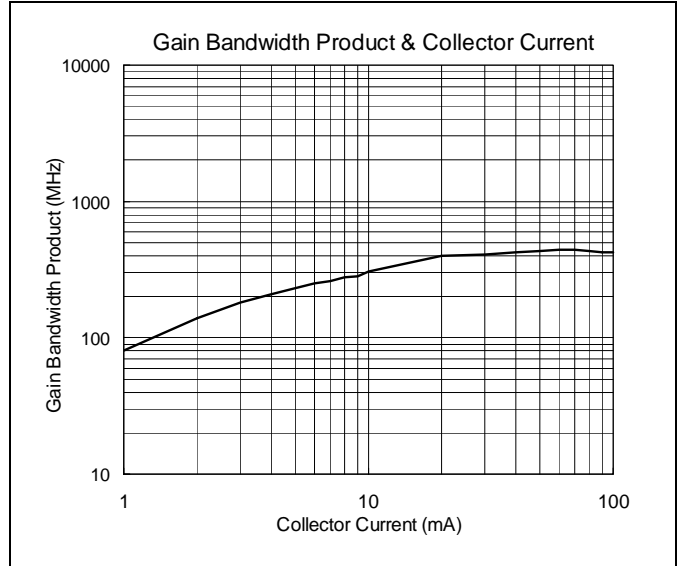
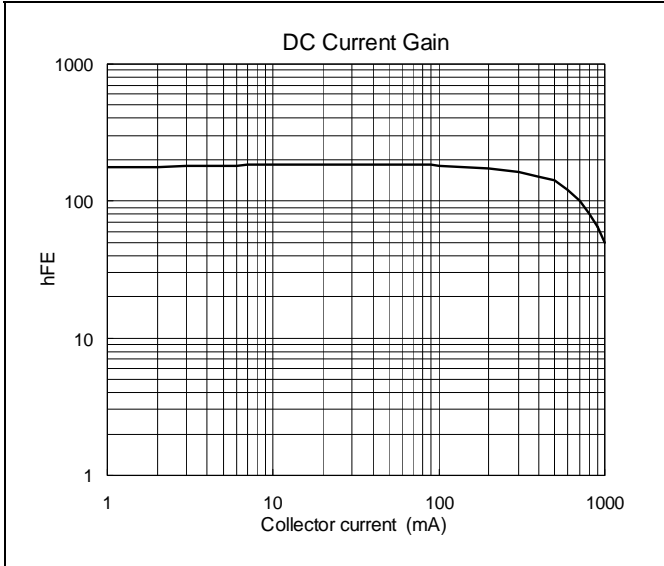
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	75	-	-	V	I <sub>C</sub> =10uA
*BV <sub>CEO</sub>	40	-	-	V	I <sub>C</sub> =100mA
BV <sub>EBO</sub>	6	-	-	V	I <sub>E</sub> =10uA
I <sub>CBO</sub>	-	-	10	nA	V <sub>CB</sub> =60V
I <sub>CEX</sub>	-	-	10	nA	V <sub>CB</sub> =60V, V <sub>EB(off)</sub> =3V
I <sub>EBO</sub>	-	-	50	nA	V <sub>EB</sub> =3V
*V <sub>CE(sat)1</sub>	-	-	300	mV	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA
*V <sub>CE(sat)2</sub>	-	-	1	V	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA
*V <sub>BE(sat)1</sub>	-	-	1.2	V	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA
*V <sub>BE(sat)2</sub>	-	-	2	V	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA
*h <sub>FE1</sub>	35	-	-	-	V <sub>CE</sub> =10V, I <sub>C</sub> =100uA
*h <sub>FE2</sub>	50	-	-	-	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA
*h <sub>FE3</sub>	75	-	-	-	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA
*h <sub>FE4</sub>	100	-	300	-	V <sub>CE</sub> =10V, I <sub>C</sub> =150mA
*h <sub>FE5</sub>	40	-	-	-	V <sub>CE</sub> =10V, I <sub>C</sub> =500mA
*h <sub>FE6</sub>	50	-	-	-	V <sub>CE</sub> =1V, I <sub>C</sub> =150mA
f <sub>T</sub>	300	-	-	MHz	I <sub>C</sub> =20mA, V <sub>CE</sub> =20V, f=100MHz

\*Pulse Test: Pulse Width ≤380us, Duty Cycle ≤2%





### Characteristics Curve





### TO-92 Dimension

3-Lead TO-92 Plastic Package  
HSMC Package Code: A

**Marking:**

Pb Free Mark  
 Pb-Free: "●" (Note)  
 Normal: None

Date Code      Control Code

Note: Green label is used for pb-free packing

Pin Style: 1. Emitter 2. Collector 3. Base

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	4.33	4.83
B	4.33	4.83
C	12.70	-
D	0.36	0.56
E	-	*1.27
F	3.36	3.76
G	0.36	0.56
H	-	*2.54
I	-	*1.27
$\alpha 1$	-	*5°
$\alpha 2$	-	*2°
$\alpha 3$	-	*2°

\*: Typical, Unit: mm

### TO-92 Taping Dimension

DIM	Min.	Max.
A	4.33	4.83
D	3.80	4.20
D1	0.36	0.53
D2	4.33	4.83
F1, F2	2.40	2.90
H	15.50	16.50
H1	8.50	9.50
H2	-	1
H2A	-	1
H3	-	27
H4	-	21
L	-	11
L1	2.50	-
P	12.50	12.90
P1	5.95	6.75
P2	50.30	51.30
T	-	0.55
T1	-	1.42
T2	0.36	0.68
W	17.50	19.00
W1	5.00	7.00

Unit: mm

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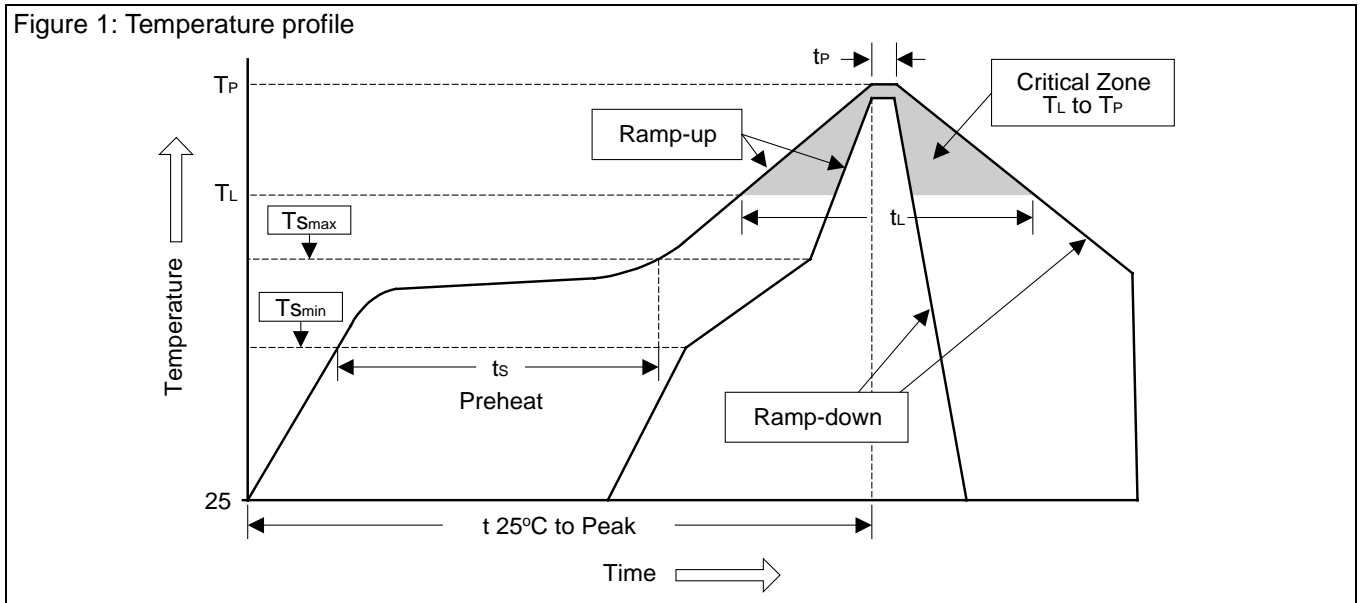
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## Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_P$ )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min ( $T_{Smin}$ )	100°C	150°C
- Temperature Max ( $T_{Smax}$ )	150°C	200°C
- Time (min to max) ( $t_s$ )	60~120 sec	60~180 sec
$T_{Smax}$ to $T_L$		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature ( $T_L$ )	183°C	217°C
- Time ( $t_L$ )	60~150 sec	60~150 sec
Peak Temperature ( $T_P$ )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature ( $t_P$ )	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec